

8/27/2003

SC12804TP

PTO/SB/08A (04-03)

Substitute for form 1449A/PTO		<i>Complete If Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>		Application Number	101650,002
		Filing Date	Concurrently Herewith 8/27/2003
		First Named Inventor	Varughese Mathew et al.
		Group Art Unit	2825
		Examiner Name	C. Everhart
Sheet	of	Attorney Docket Number	SC12804TP

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>Cyme</i>	AC	Itabashi <i>et al.</i> , "Electroless Deposited CoWB for Copper Diffusion Barrier Metal," <i>Proceedings of the IEEE 2002 International Interconnect Technology Conference</i> (Cat. No. 02EX519), 2002, pp. 285-287.	

Examiner Signature	<i>C. Guenard</i>	Date Considered	10-29-04
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SC12804TP

PTO/SB/08A (04-03)

REPLACEMENT OF FORM 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet		of	Complete if Known		
			Application Number	10/650,002	
			Filing Date	August 27, 2003	
			First Named Inventor	Vanughese Mathew et al.	
			Group Art Unit	1762 2825	
			Examiner Name	Unassigned C. Everhart	
			Attorney Docket Number	SC12804TP	

**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number -Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CYME	BA	6,528,409 B1	03/04/2003	Lopatin et al.	—
CYME	BB	2003/0111729 A1	06/19/2003	Leu et al.	—

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
CYME	BC	Duch et al., "Development and Characterization of Co-Ni Alloys for Microsystems Applications," <i>Journal of the Electrochemical Society</i> , 2002, 149(4), pp. C201-C208.	
CYME	BD	Homma et al., "Microstructural Study of Electroless-Plated CoNiP Ternary Alloy Films for Perpendicular Magnetic Recording Media," <i>IEEE Transactions on Magnetics</i> , November 1991, 27(6), pp. 4909-4911.	
CYME	BE	Kohn et al., "Characterization of Electroless Deposited Co(W,P) Thin Films for Encapsulation of Copper Metallization," <i>Materials Science and Engineering</i> , 2001, A302, pp. 18-25.	
CYME	BF	Kohn et al., "Evaluation of Electroless Deposited Co(W,P) Thin Films as Diffusion Barriers for Copper Metallization," <i>Microelectronic Engineering</i> , 2001, 55, pp. 297-303.	
CYME	BG	Petrov et al., "Electrochemical Study of the Electroless Deposition of Co(P) and Co (W,P) Alloys," <i>Journal of the Electrochemical Society</i> , 2002, 149(4), C187-C194.	
CYME	BH	Osaka et al., "Fabrication of Electroless NiReP Barrier Layer on SiO <sub>2</sub> without Sputtered Seed Layer," <i>Electrochemical and Solid-State Letters</i> , 2002, 5(1), pp. C7-C10.	
CYME	BI	O'Sullivan et al., "Electrolessly Deposited Diffusion Barriers for Microelectronics," <i>IBM Journal of Research and Development</i> , September 1998, Vol. 42, No. 5, pp. 607-620.	
CYME	BJ	Segawa et al., "Manufacturing-ready Selectivity of CoWP Capping on Damascene Copper Interconnects," <i>Advanced Metallization Conference 2001, AMC 2001 Proceedings of the Conference</i> , pp. 567-572.	
CYME	BK	Shacham-Diamond et al., "Electroless Co(W,P) and Co (Mo,P) Deposition for Cu Metallization Applications," <i>IEEE, 2001 6th International Conference on Solid State and Integrated Circuit Technology</i> , Vol. 1, 2001, pp. 410-415.	
CYME	BL	Shacham-Diamond et al., "Electroless Deposition of Thin-Film Cobalt-Tungsten-Phosphorus Layers Using Tungsten Phosphoric Acid (H <sub>3</sub> [P(W <sub>3</sub> O <sub>10</sub> ) <sub>4</sub> ]) for ULSI and MEMS Application," <i>Journal of the Electrochemical Society</i> , 2001, 148(3), pp. C162-C167.	
CYME	BM	Shacham-Diamond et al., "Material Properties of Electroless 100-200 nm Thick CoWP Films," <i>Electrochemical Technology Applications in Electronics Proceedings of the Third International Symposium Electrochemical Society Proceedings</i> , 2000, Vol. 99-34, pp. 102-110.	

Examiner Signature	C. Everhart	Date Considered	10-29-04
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